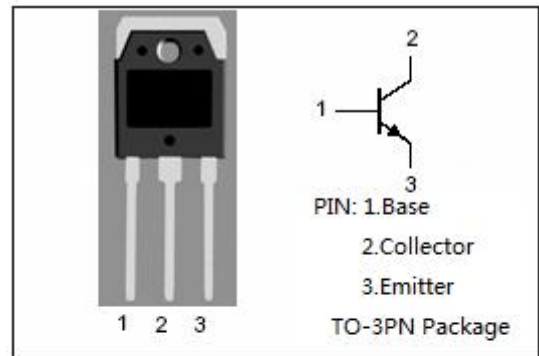


isc Silicon NPN Power Transistor
BUW133A
DESCRIPTION

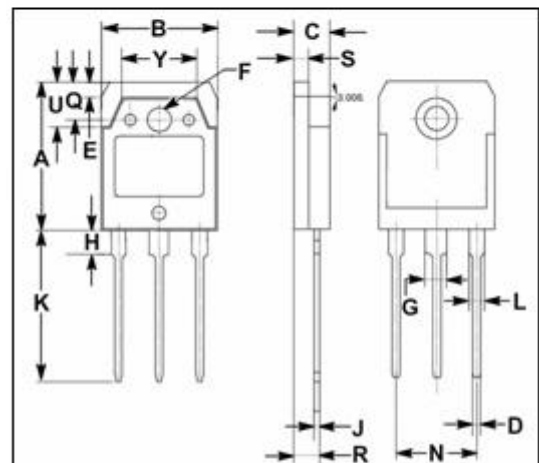
- High Switching Speed
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 500V$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in very fast switching applications in inductive circuits.


ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	MAX	UNIT
V_{CES}	Collector- Emitter Voltage ($V_{BE} = 0$)	1000	V
V_{CEO}	Collector-Emitter Voltage	500	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Collector Current-Peak	20	A
I_B	Base Current	10	A
I_{BM}	Base Current-Peak	15	A
P_C	Collector Power Dissipation @ $T_C=25^\circ C$	135	W
T_j	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$



DIM	mm	
	MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.93	$^\circ C/W$

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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 50mA ; I _B = 0	500			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 1A			2.5	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 10A; I _B = 2A			3.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 10A; I _B = 2A			1.5	V
I _{CBO}	Collector-Base Cutoff Current	V _{CB} =V _{CBO} ; I _E = 0 V _{CB} =V _{CBO} ; I _E = 0; T _J =100°C			0.25 1.5	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C = 0			1	mA
h _{FE}	DC Current Gain	I _C = 15A ; V _{CE} = 5V	5			
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 10V; f _{test} = 1kHz			400	pF

Switching Times , Resistive Load

t _{on}	Turn-On Time	I _C = 10A ; I _{B1} = 1A; I _{B2} = -2A		0.4		μ s
t _{stg}	Storage Time			1.3		μ s
t _f	Fall Time			0.15		μ s

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